

EVVOSEMI[®]

THINK CHANGE DO



ESD



TVS



MOS



LDO



Diode



Sensor



DC-DC

Product Specification

▶ Domestic	Part Number	EV2SB1260-X-SB
▶ Overseas	Part Number	2SB1260-X
▶ Equivalent	Part Number	2SB1260-X

"SB" means SOT-89

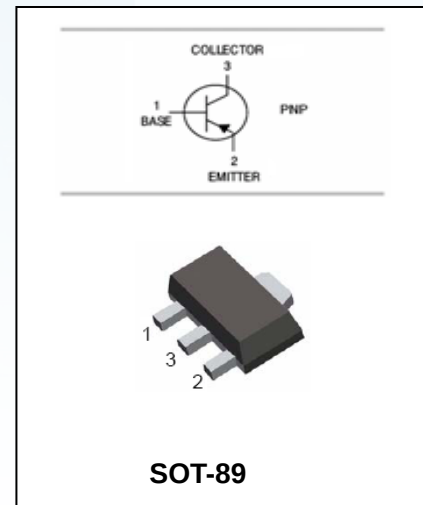
EV is the abbreviation of name EVVO

FEATURES

- High breakdown voltage and high current.
 $BV_{CEO} = -80V, I_C = -1A$
- Good h_{FE} VLinearity.
- Low $V_{CE(sat)}$.
- Complements the 2SD1898.

APPLICATIONS

- Epitaxial planar type PNP silicon transistor



MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-80	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current –DC -Pulse	-1 -2	A
P_c	Collector power Dissipation	0.5	W
T_j	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55 to +150	°C

***1:** When mountef on a 40*40*0.7mm ceramic board.

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -50\mu A$ $I_E = 0$	-80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA$ $I_B = 0$	-80			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -50\mu A$ $I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -60V$ $I_E = 0$			-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4V$, $I_C = 0$			-1	μA
DC current gain	h_{FE}	$V_{CE} = -3V$ $I_C = -0.1A$	120		390	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500mA$ $I_B = -50mA$			-0.4	V
Output Capacitance	C_{obo}	$V_{CB} = -10V$ $f = 1.0MHz$ $I_E = 0$	-	20		pF

CLASSIFICATION h_{FE}

Rank	EV2SB1260-Q-SB	EV2SB1260-R-SB
Range	120-270	180-390

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

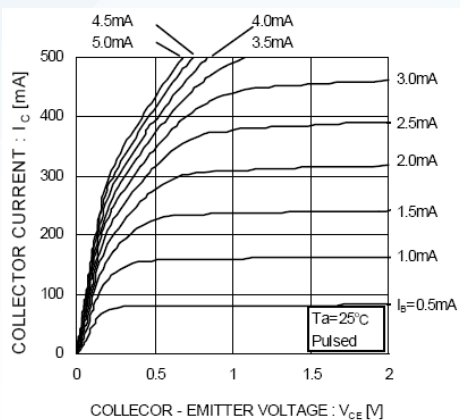


Fig.1 Ground Emitter Output Characteristics

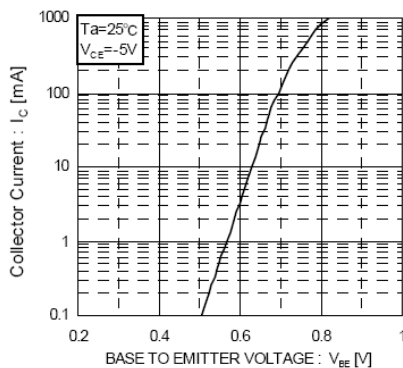


Fig.2 Grounded Emitter Propagation Characteristics

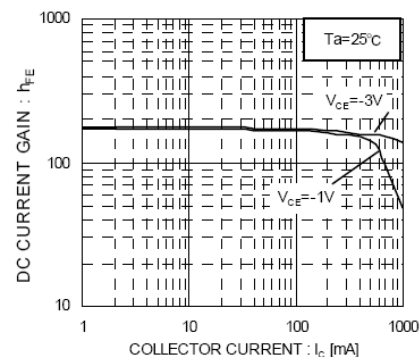


Fig.3 DC Current Gain vs Collector Current

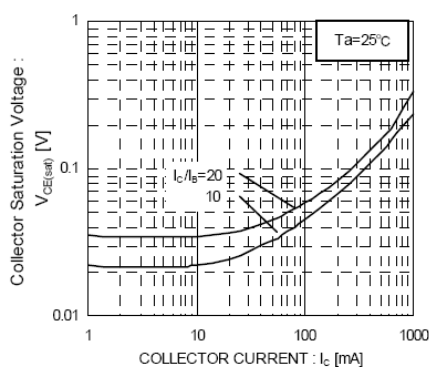


Fig.4 Collector-Emitter Saturation Voltage vs Collector Current

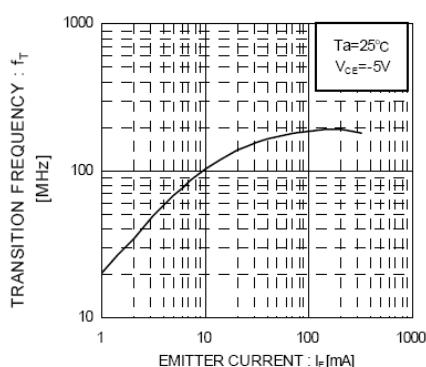
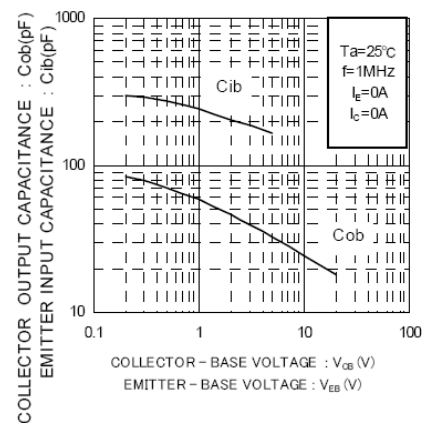


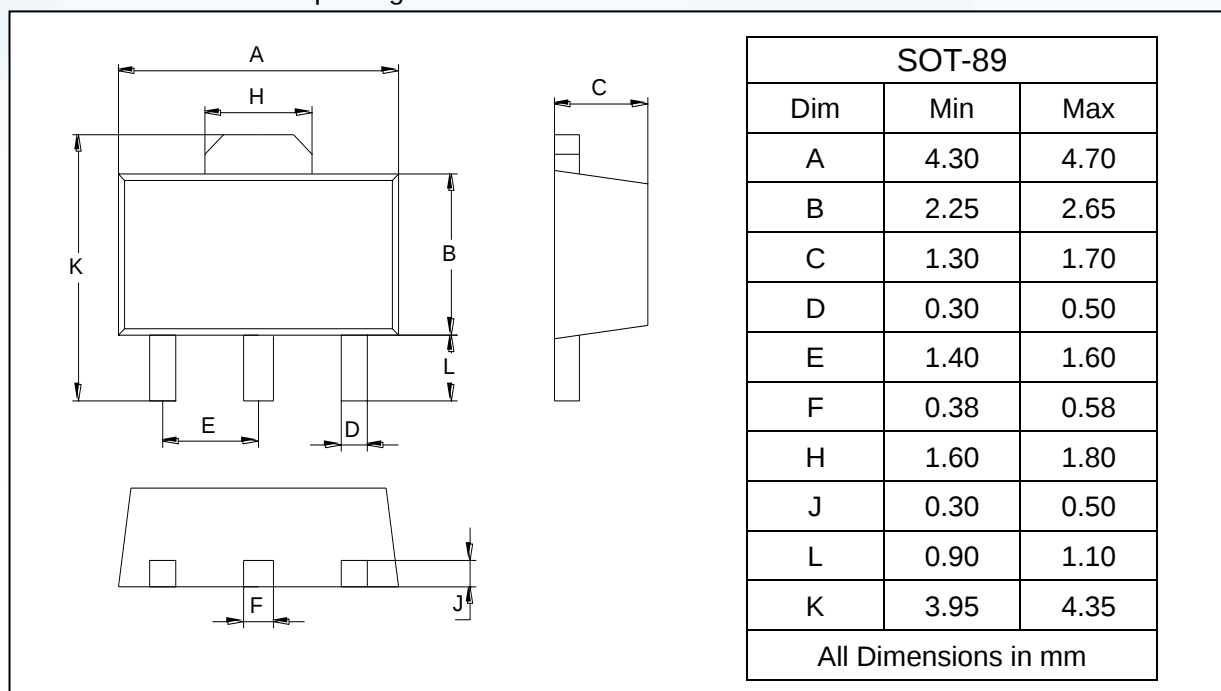
Fig.5 Transition Frequency vs Emitter Current

Fig.6 Emitter Input Capacitance vs. Emitter-Base Voltage
Collector Output Capacitance vs. Collector-Base

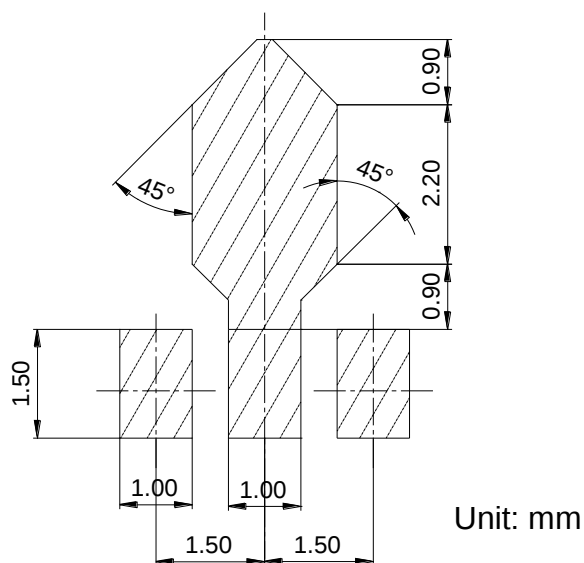
PACKAGE OUTLINE

Plastic surface mounted package

SOT-89



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
2SB1260	SOT-89	1000 pcs / Tape & Reel

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